

Consorzio Nazionale Interuniversitario per la Nanoelettronica IUNET

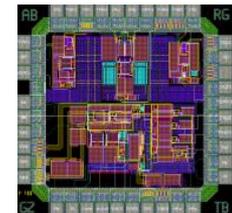
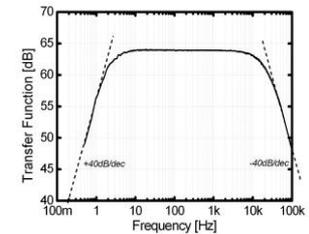
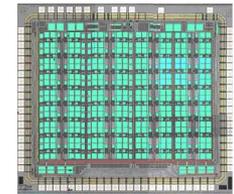
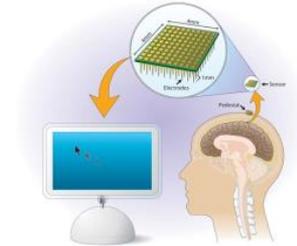
MICROELECTRONICS FOR BRAIN MACHINE INTERFACE

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IUNET – Politecnico di Milano



Outline

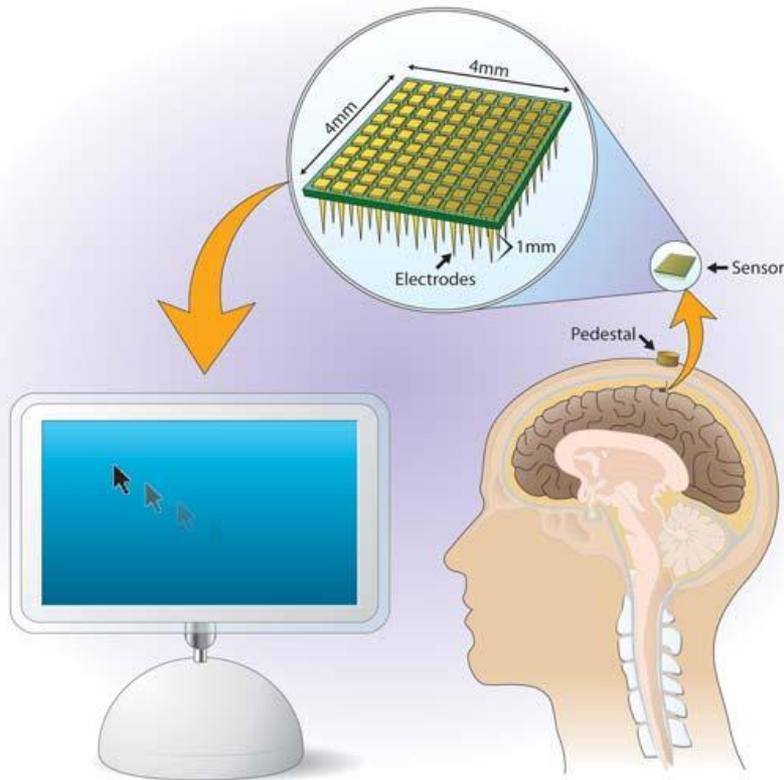
- The Brain Machine Interface concept
- Front-end amplifier design
- Experimental results
- Ongoing projects
- Conclusions



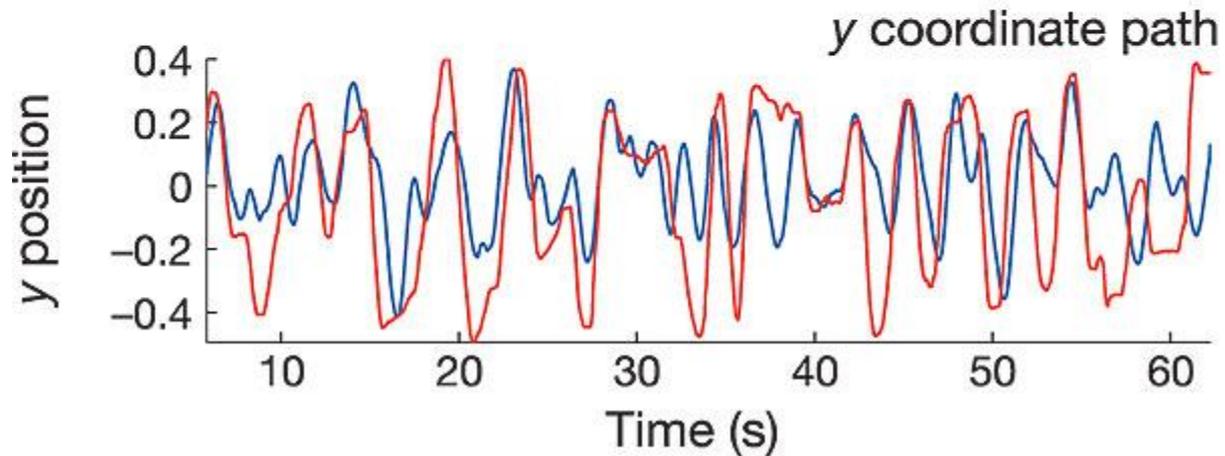
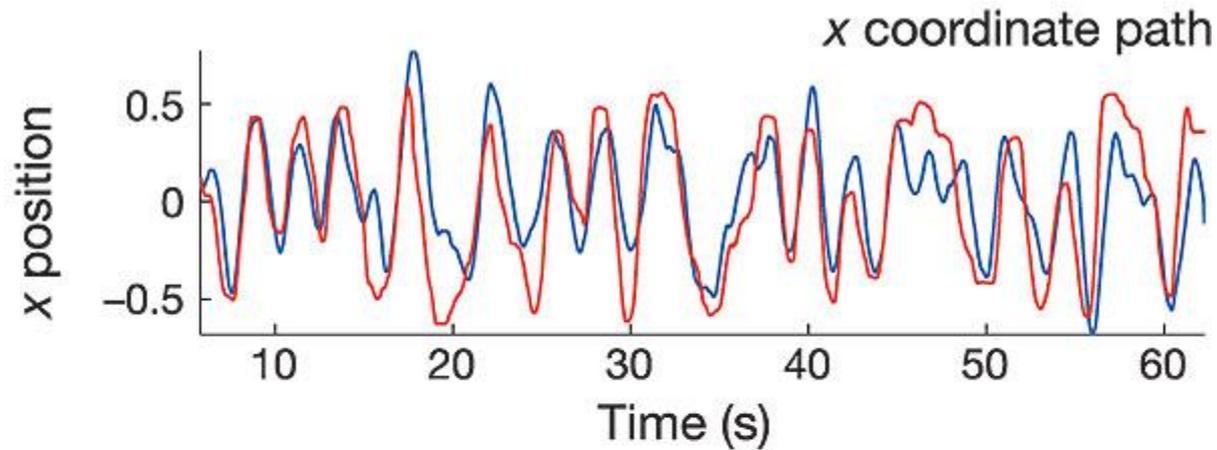
Brain Machine Interface (BMI)



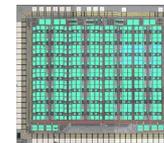
The BMI concept



Proof of concept



The goal

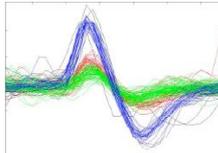


The project goal is to shrink bulky instruments into implantable integrated circuits

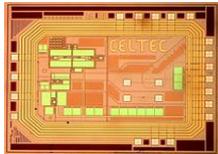
The BMI electronics



Robotic arm



Processing



Signal readout



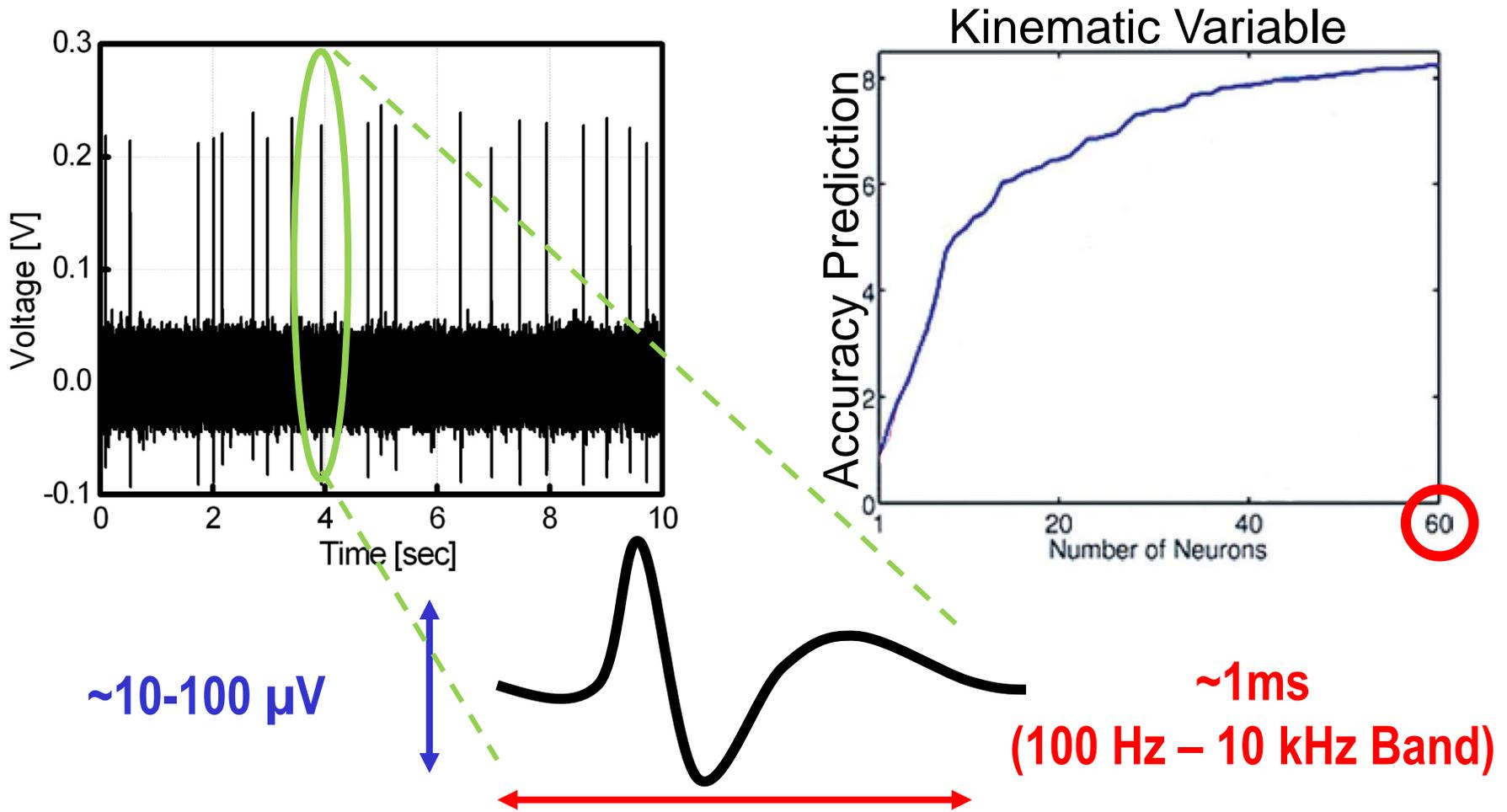
Multi Electrodes



Brain



Neural signal

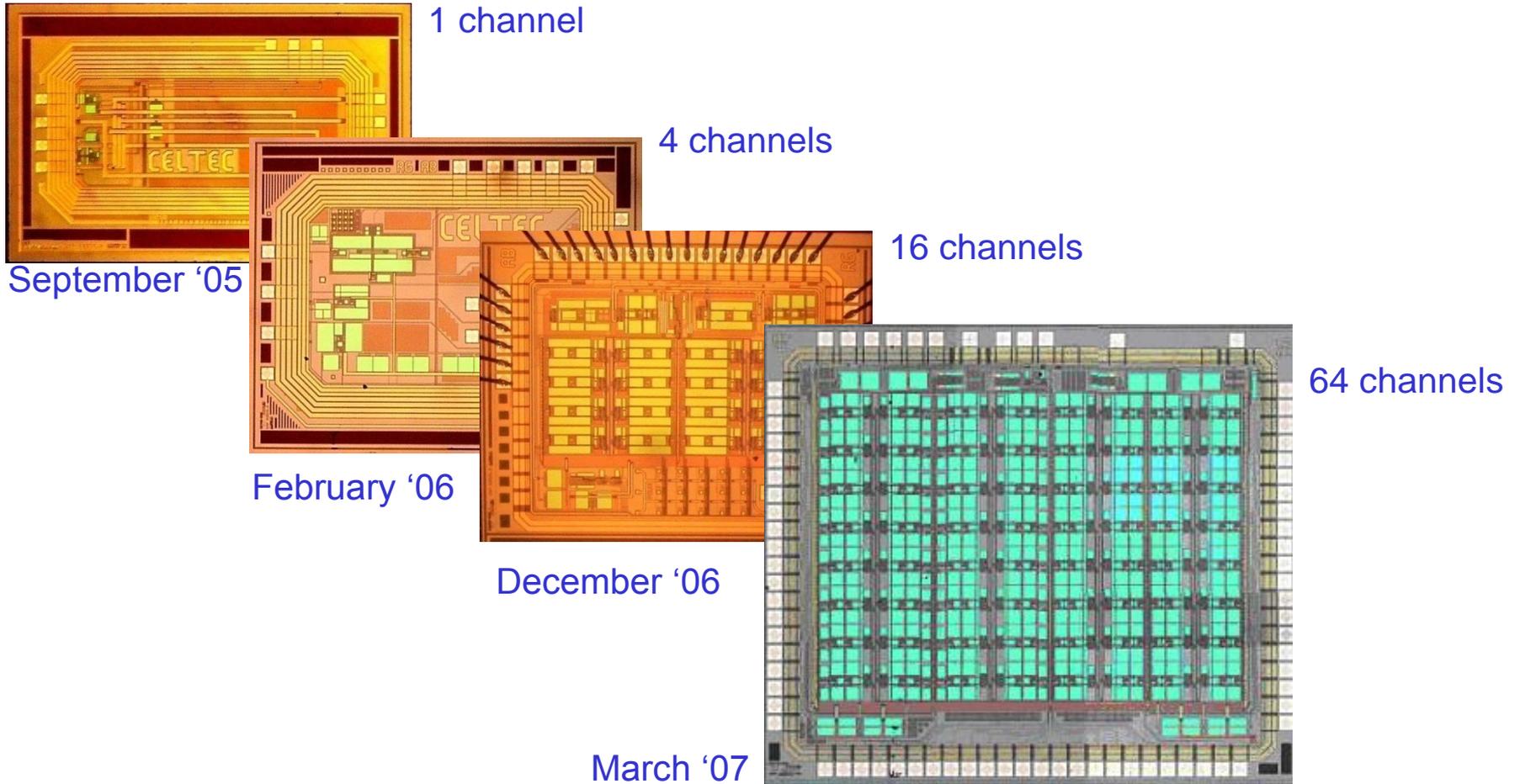


Amplifier requirements

- Low-noise amplifier ($< 5 \mu\text{V}_{\text{rms}}$)
- Low-power (to prevent tissue damage)
- Eliminate electrode-tissue DC offset ($\sim 100 \text{ mV}$)
- Deliver $> 60 \text{ dB}$ gain for a signal bandwidth of 10 kHz
- High Input Impedance ($> 10 \text{ M}\Omega @ 1\text{kHz}$)



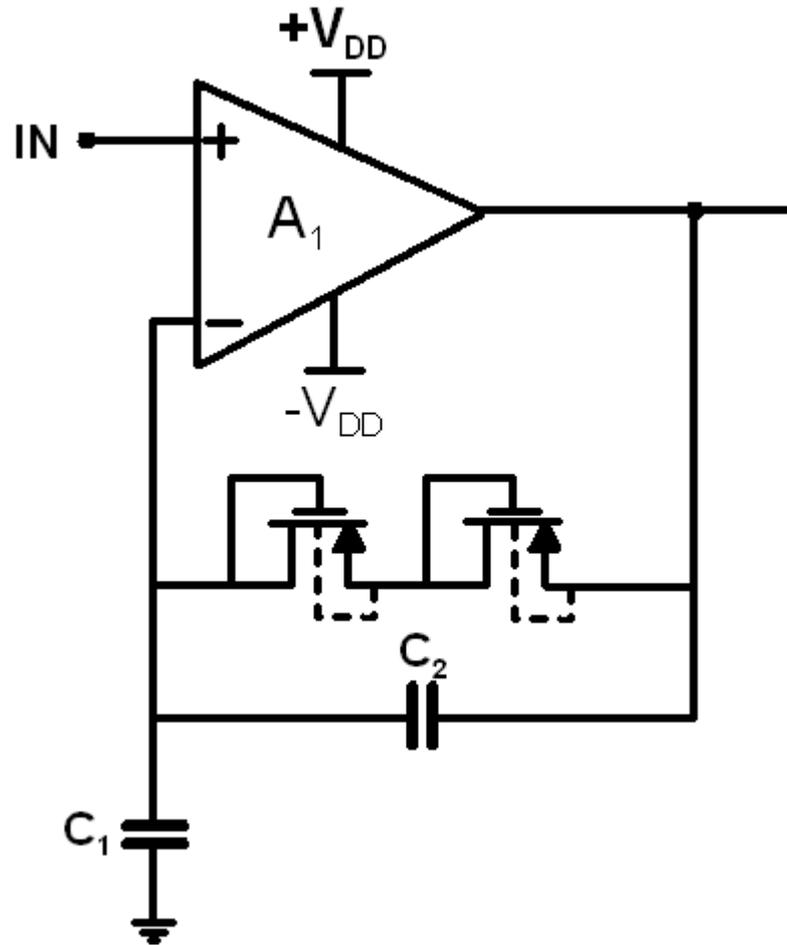
Design history



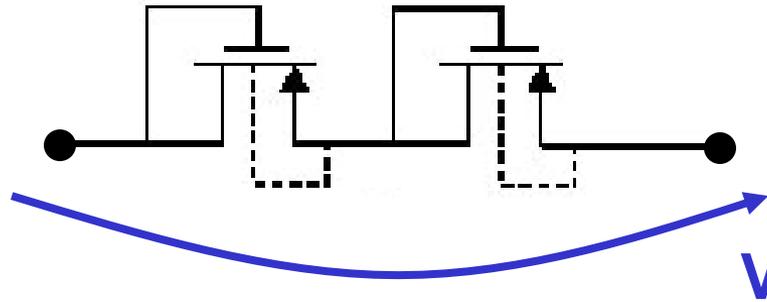
Front-end Design



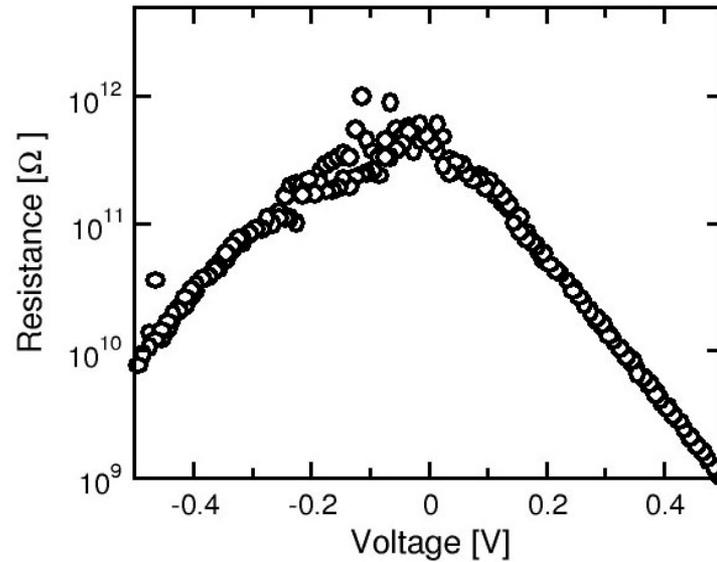
Front-end



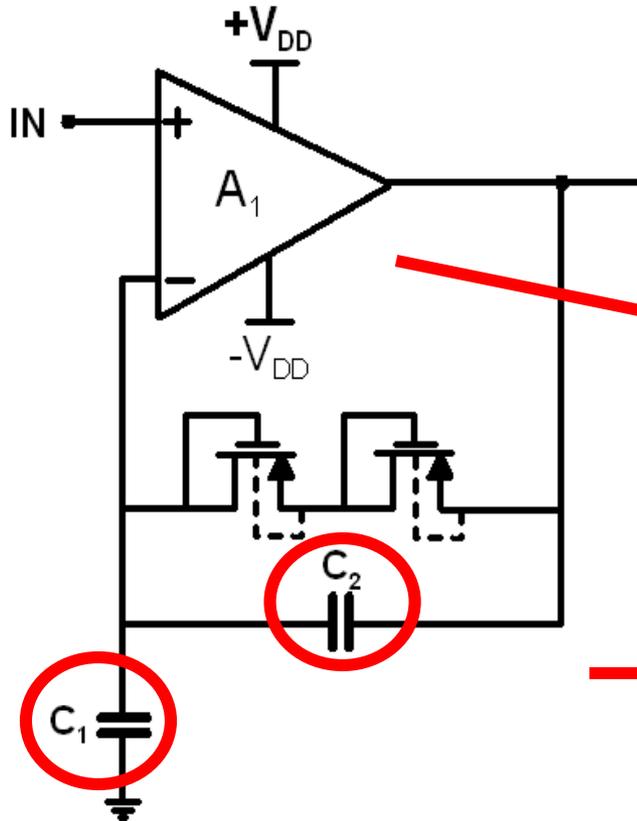
Feedback element



MOS devices
used as high-
value resistors
(Harrison, 2003)



Gain



Band-pass Filter

Low-pass pole:

– $GBWP/G_1 \sim 20 \text{ kHz}$

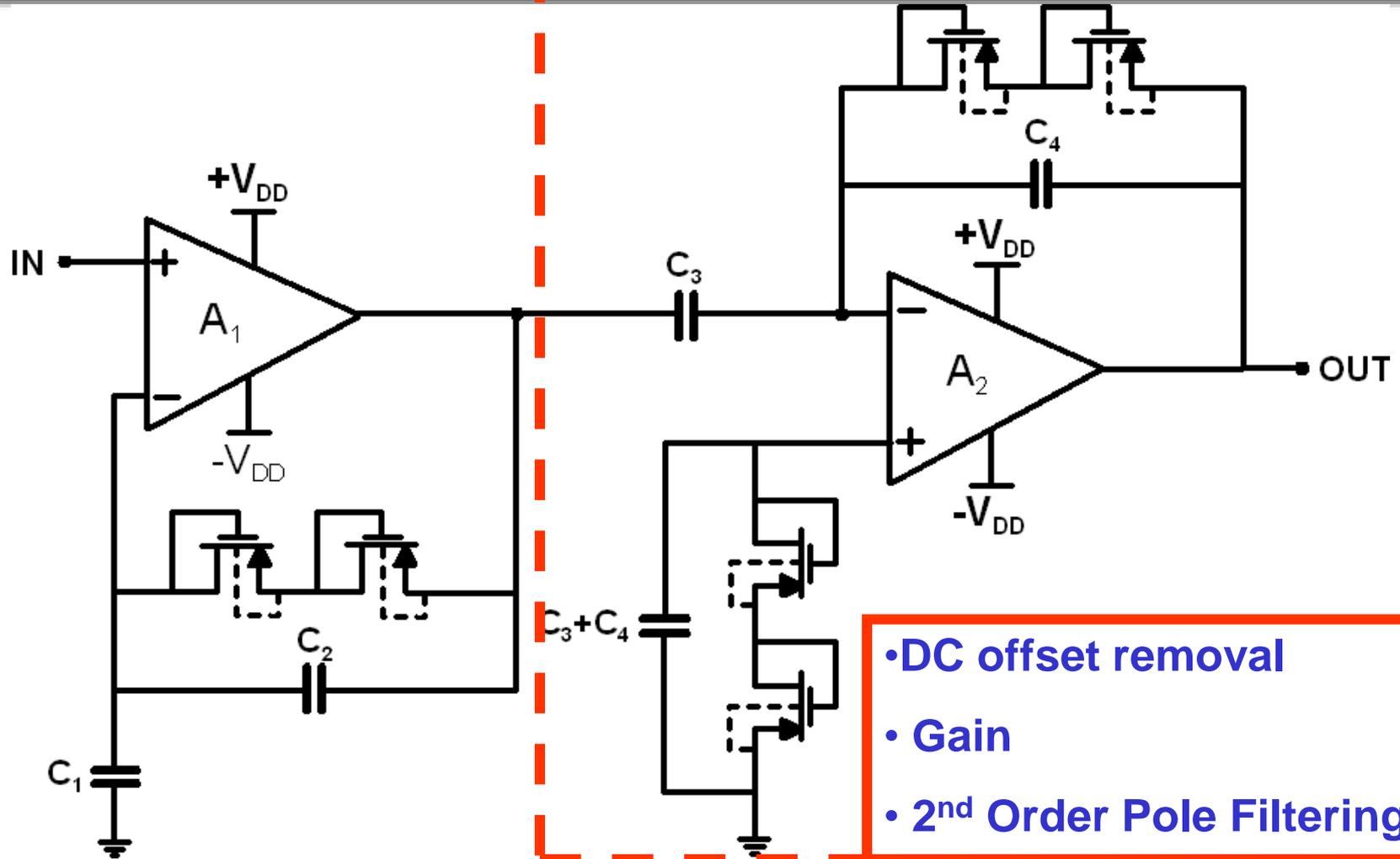
Midband Gain

$$G_1 = (C_1 + C_2)/C_2 \sim 50$$

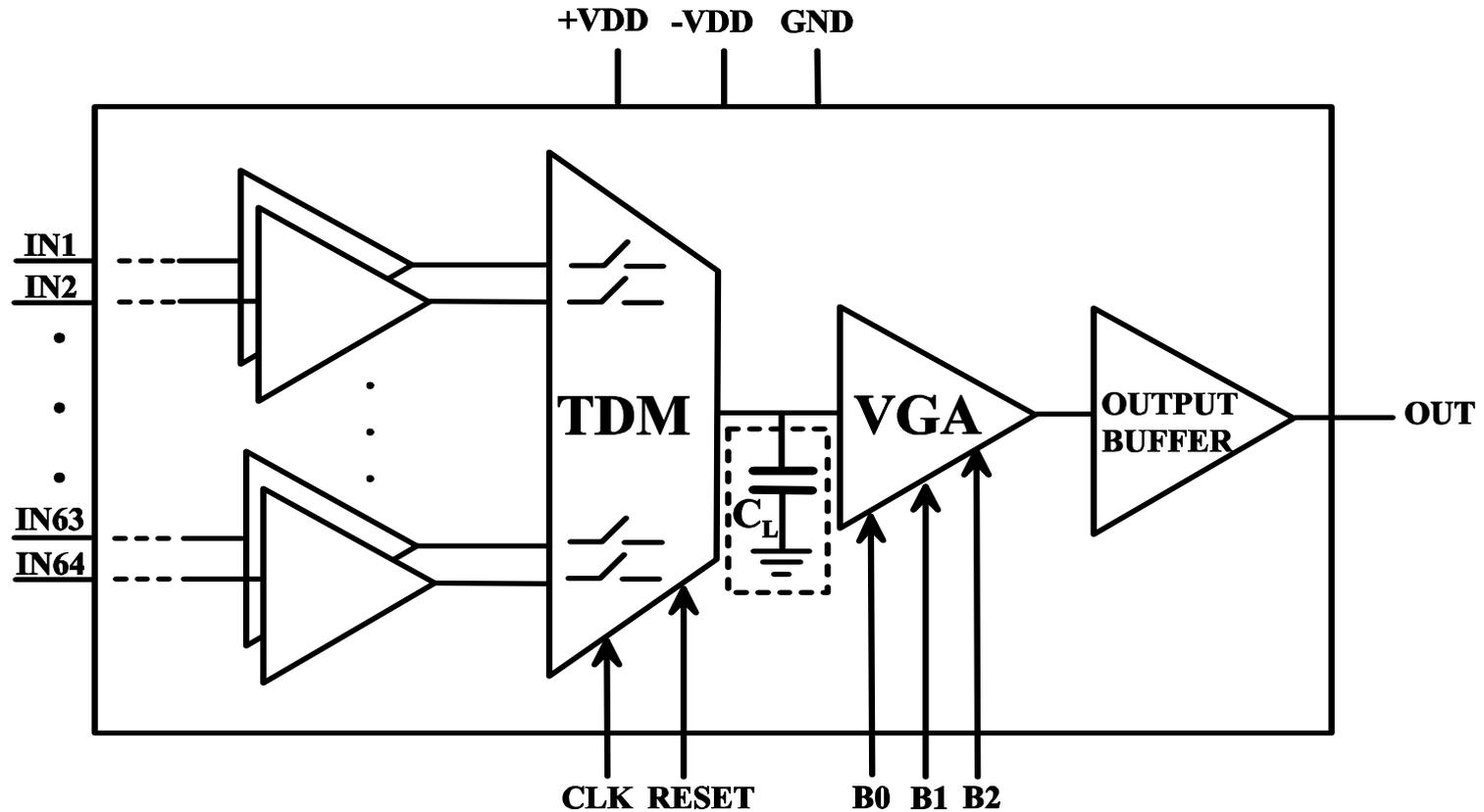
$$C_1 = 10 \text{ pF}$$

$$C_2 = 200 \text{ fF}$$

Second stage

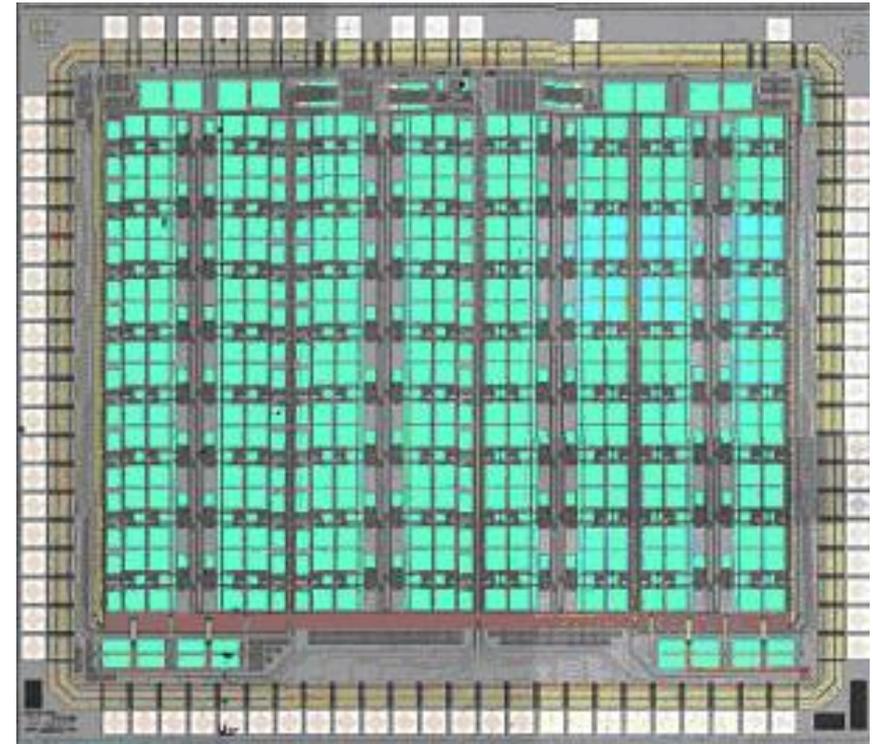
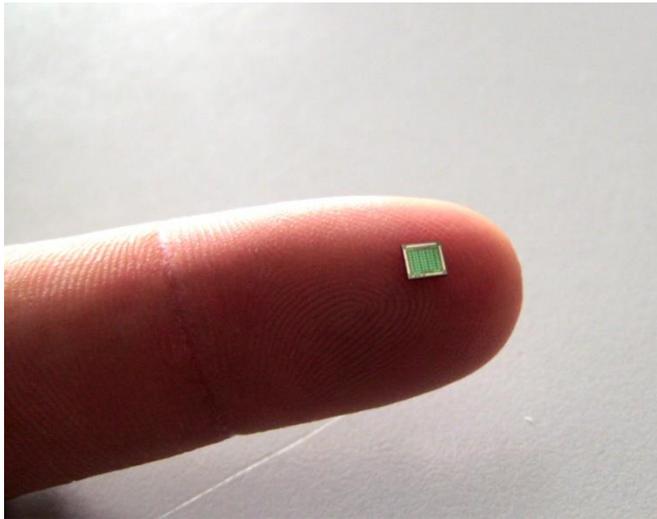


Array design



The chip

Fabricated in a 0.35- μm 2-poly,
4-metal commercial CMOS
process through CMP



Dimensions: 2.6 mm x 3 mm

Characteristics

Technology	CMOS 0.35 μ m AMS
Chip Area	8.25 mm ²
Voltage Supply	± 1.5 V
Preamplifier midband gain	64 dB
Preamplifier bandwidth	2 Hz – 20 kHz
Preamplifier input noise (100 Hz – 10 kHz)	2.9 μ V _{rms}
Buffer line settling time	100 nsec
Buffer output impedance	2 k Ω
VGA gain	0-27 dB
VGA + Output Buffer Bandwidth	> 10 MHz



Power consumption (single channel)

Current consumption	
Preamplifer (each)	45 μ A
Line Buffer (each)	45 μ A
VGA Output	270 μ A
Output Buffer	400 μ A
Total	6 mA or 18 mW

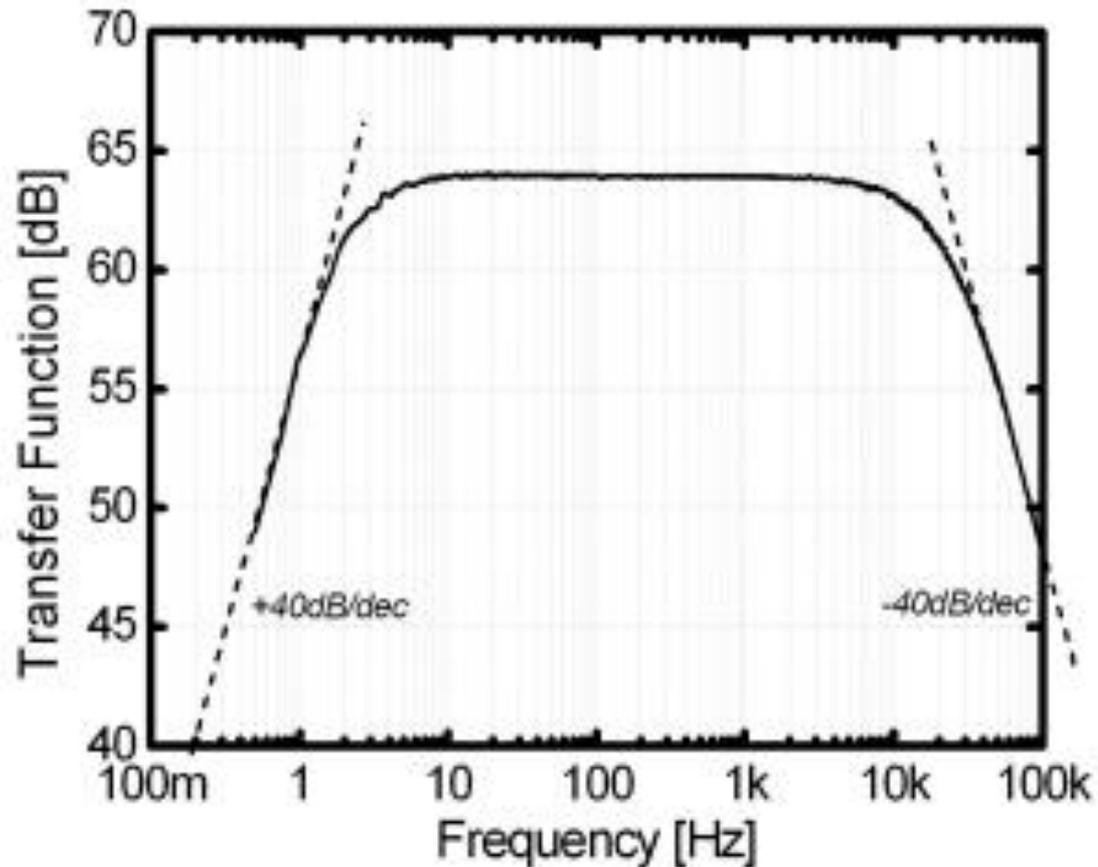
More than 20 days of continuous recording with two AA battery



Experimental Results

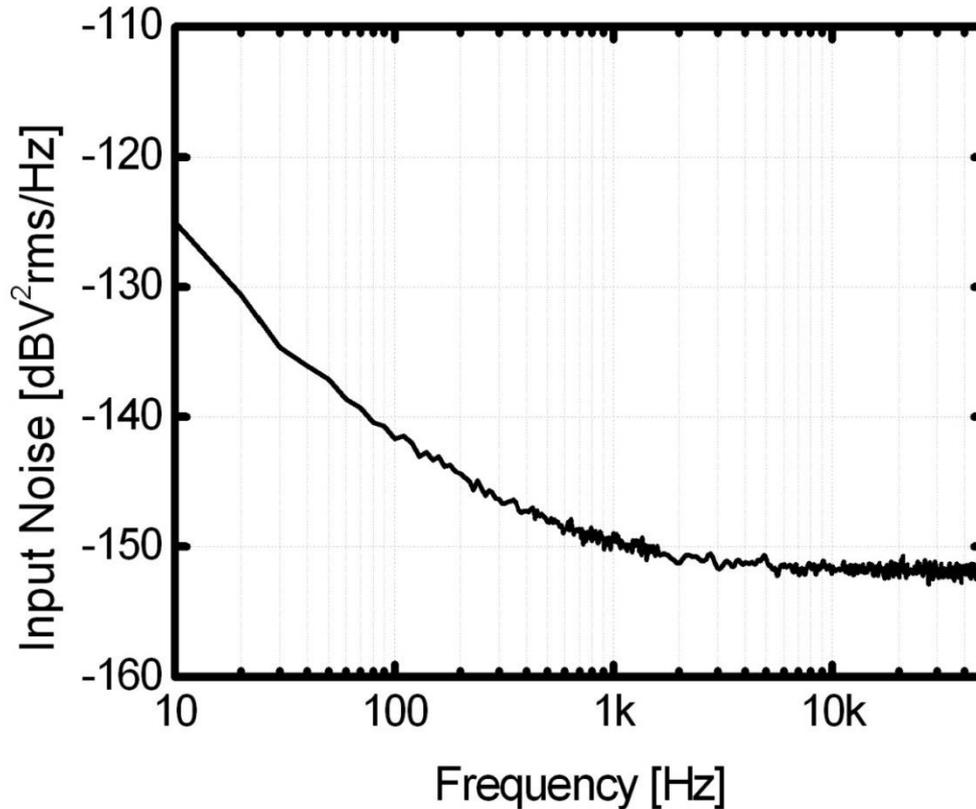


Transfer function



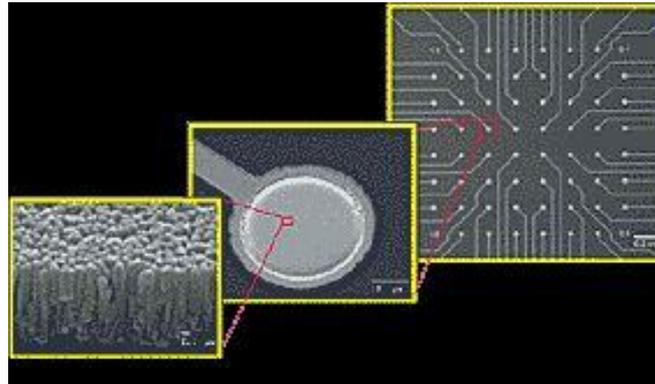
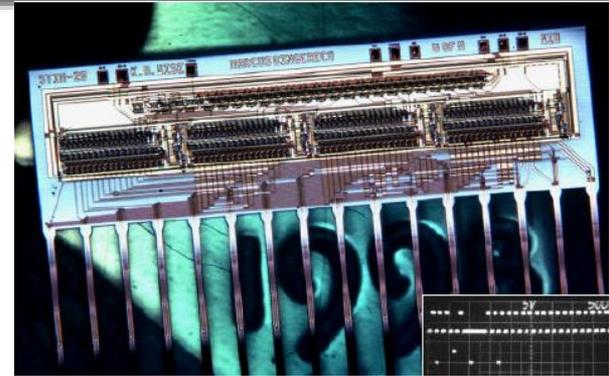
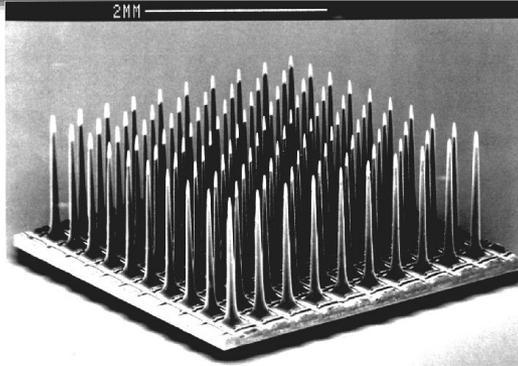
2nd order poles at 2 Hz and 20 kHz

Noise performance

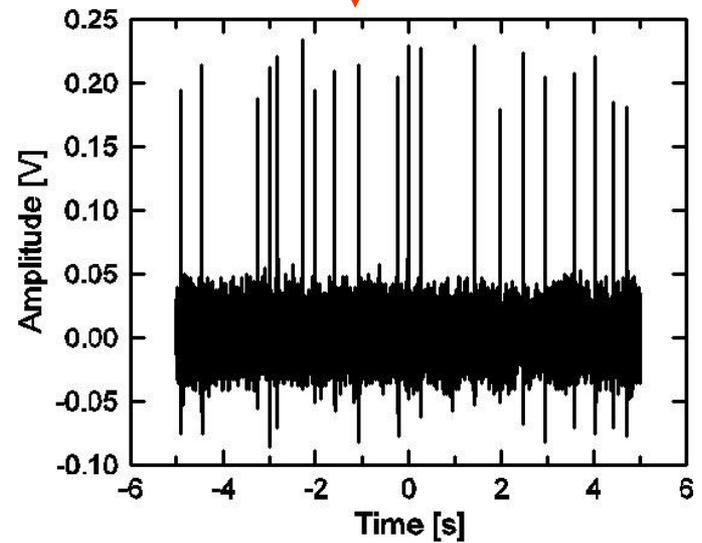
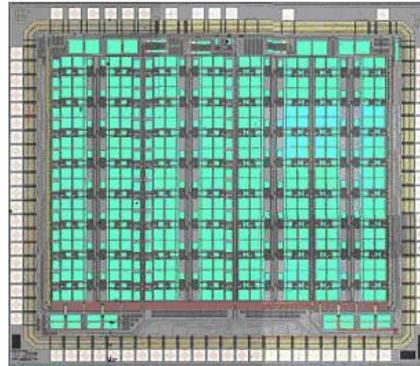
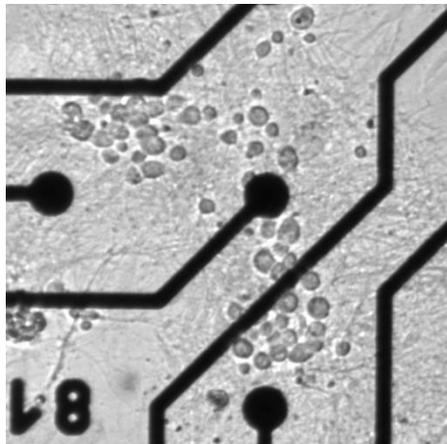


Input-referred rms noise of **2.9 μ V** (100 Hz – 10 kHz band) with **45 μ A** of current consumption

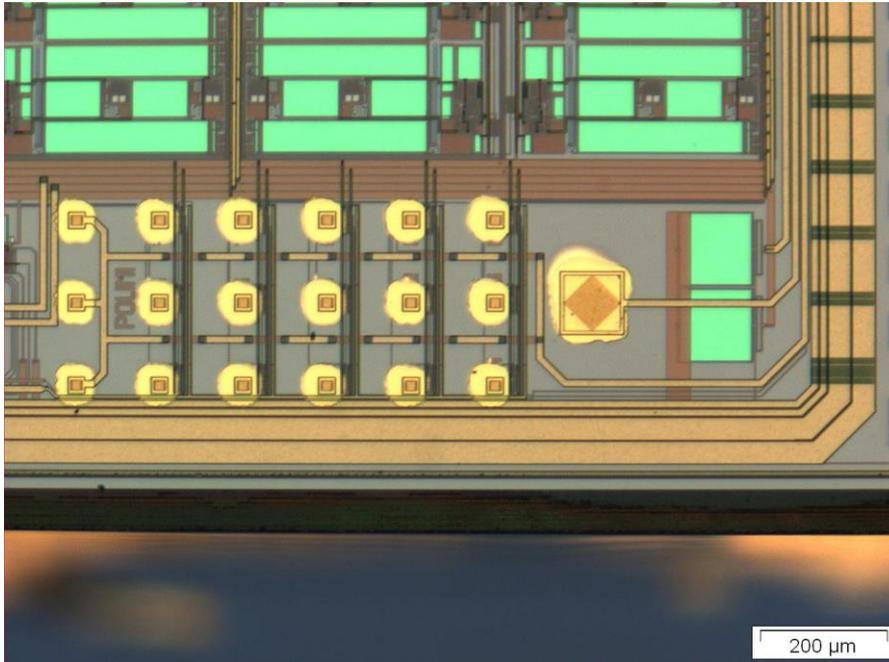
Commercial microelectrodes



Preliminary recordings (*in vitro*)



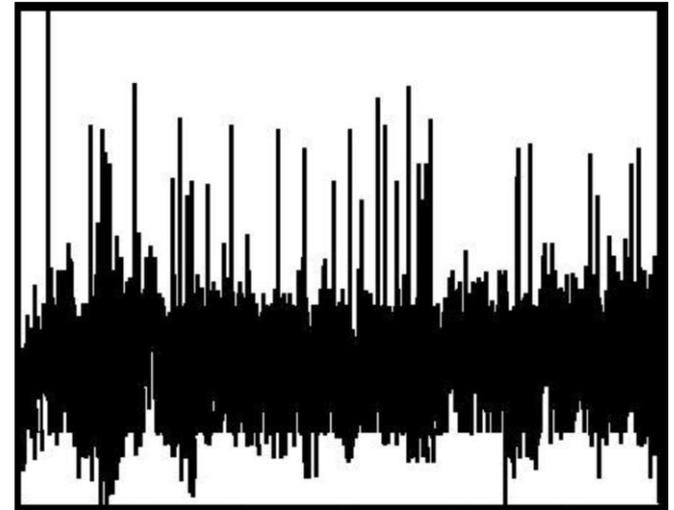
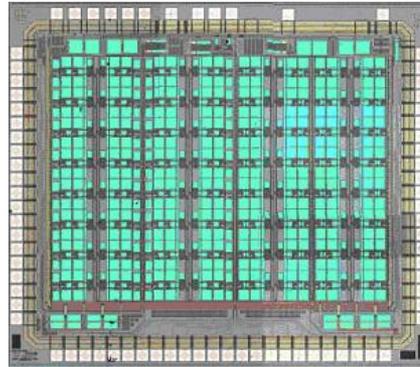
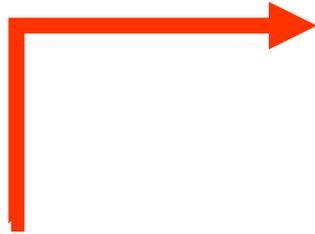
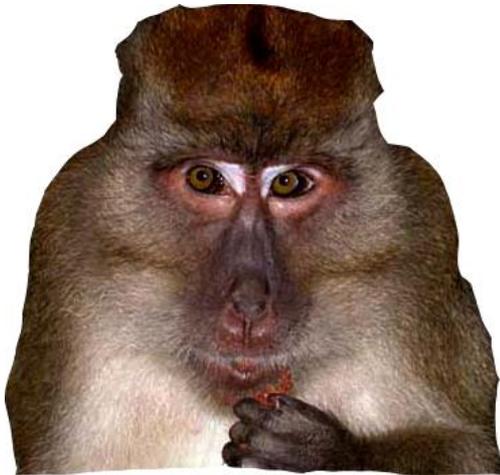
Electrode coating issue



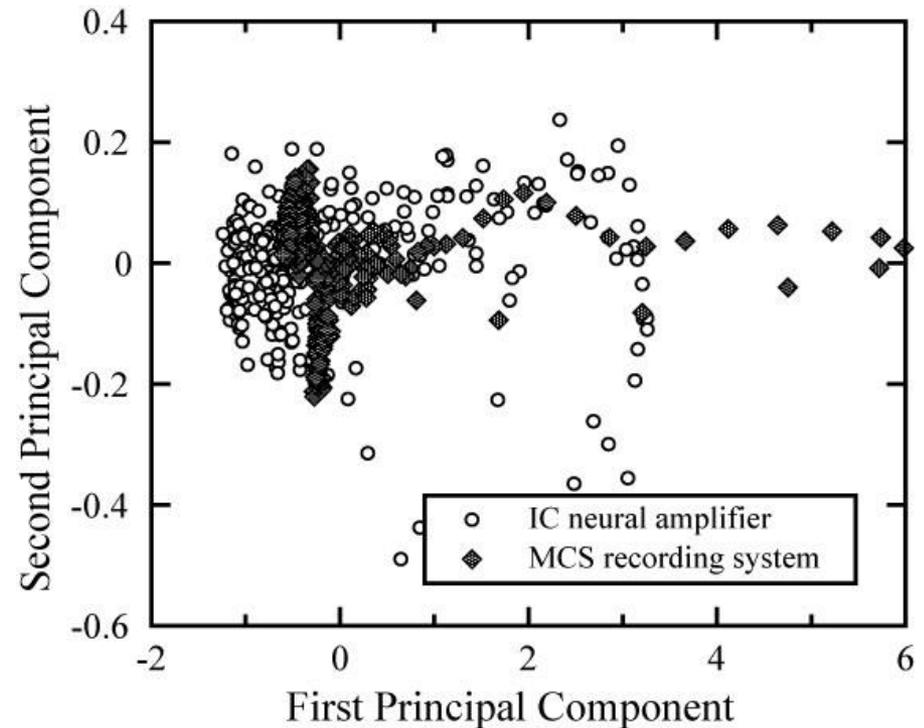
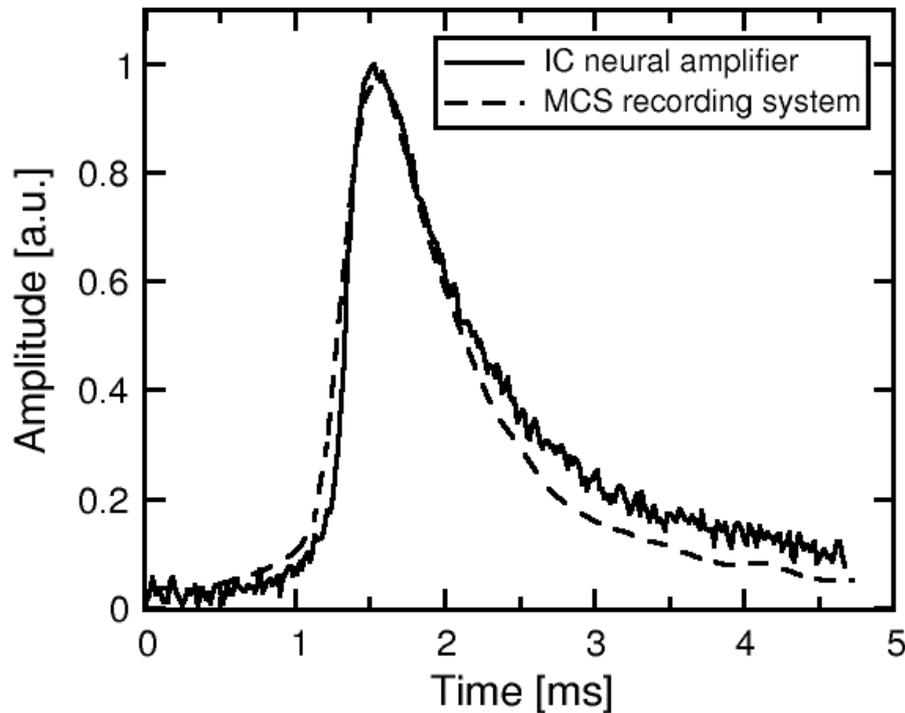
- 100 nm layer
- Mask resolution down to about 50 μm
- Lift-off technique with SU-8 masks

Electrode impedance endurance tests ongoing

Preliminary recordings (*in vivo*)



Quality of recorded data

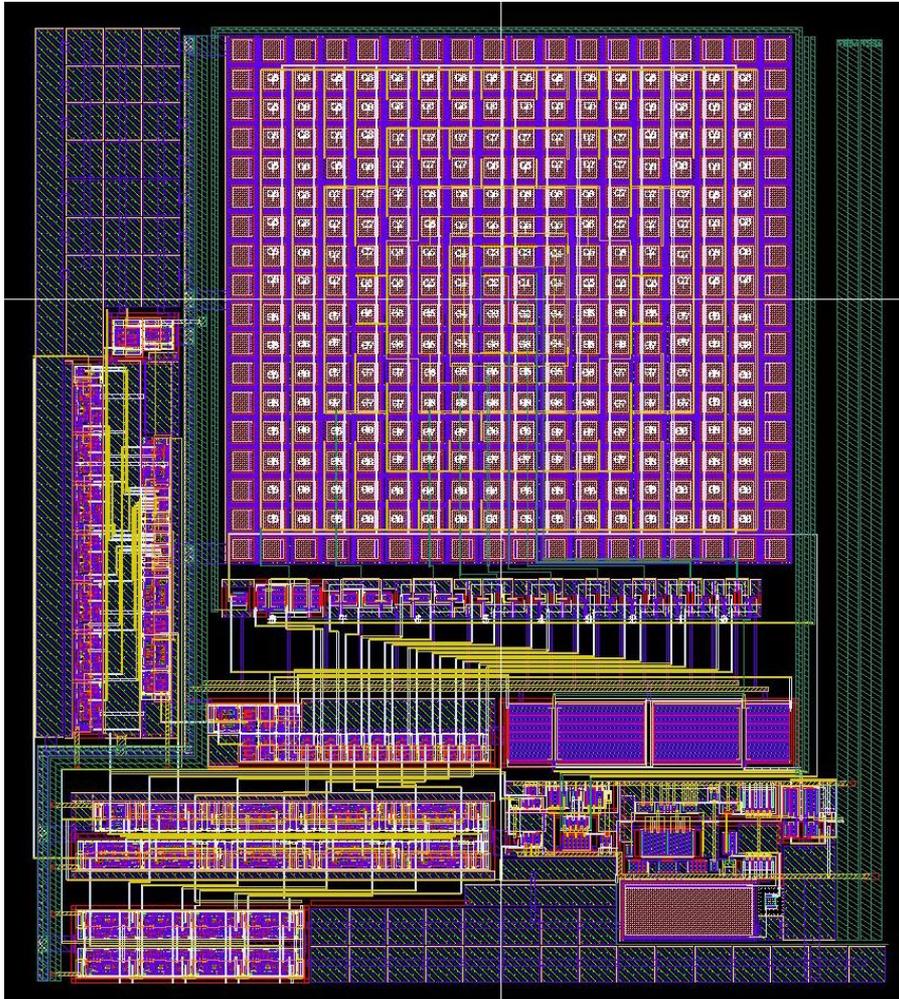


Achieved the same SNR and recording quality of bulky commercial systems (MCS)

Ongoing Projects

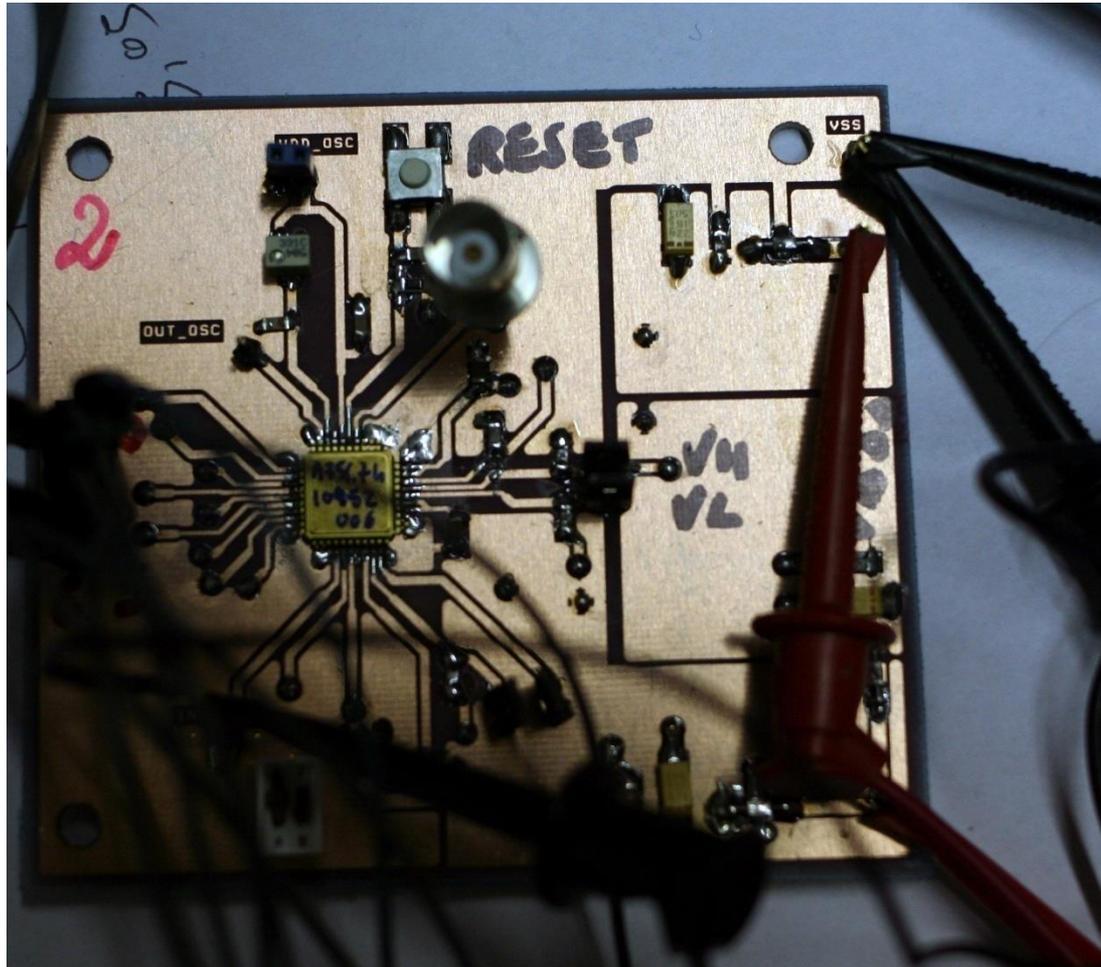


8-bit SAR ADC

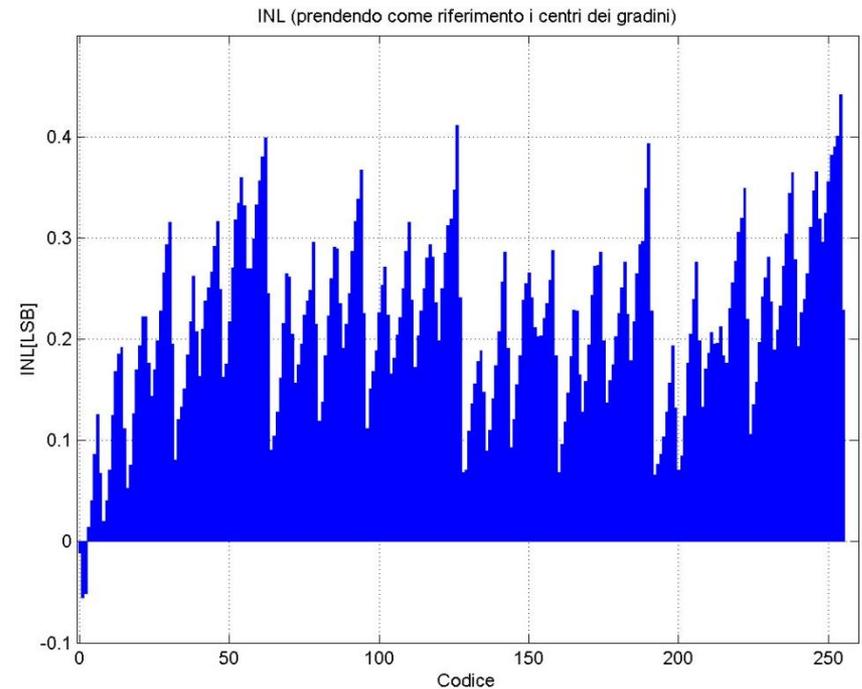
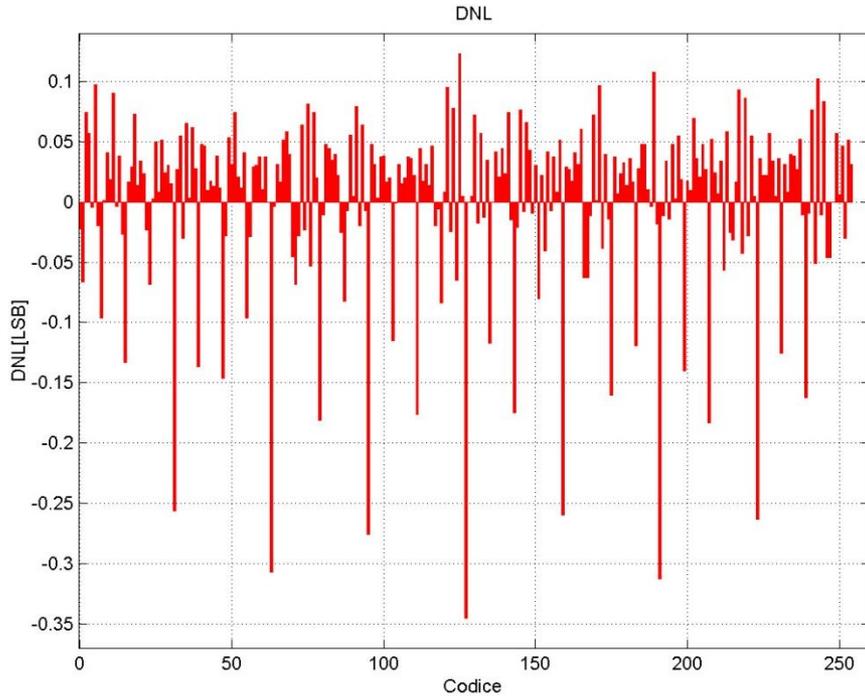


Parameter	Value
Supply voltage	3.3 V
Power	< 5 mW
Sampling Rate	1.28 MS/s (20 kS/s/Channel)
Clock Rate	20 MHz
Offset Error	< 1 LSB
V_{LSB} (electrode referred)	1 μV
Area in 0.35- μm Process	500 μm x 500 μm

ADC testing

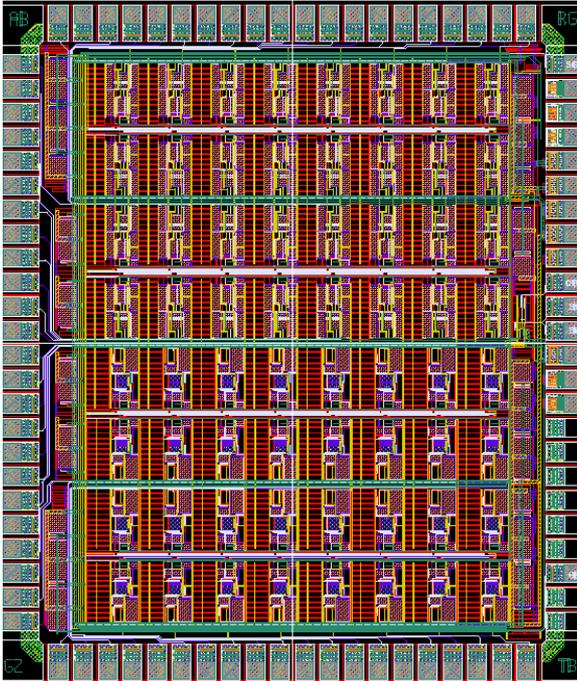


Preliminary results



DNL < 0.4 and INL \approx 0.4 LSB

Total power consumption



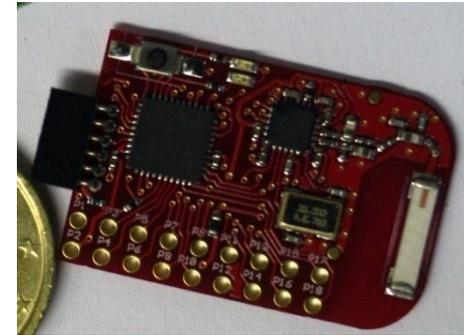
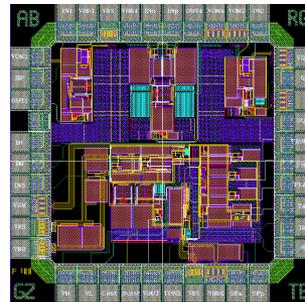
10 mW

+

10 mW

+

50 mW



Available power from inductive link \approx 100 mW

Conclusions

- 64-channel array amplifier
 - Input referred noise of 2.9 V rms (lowest in literature)
 - Band-pass filtering from 2 Hz to 20 kHz
 - 60 db midband gain
- Good recording quality in field tests
- ADC under characterization
- Analog sorting designed (to be taped out)
- Digital processing, wireless transmission and power under study

